



THE UNITED STATES PATENT AND TRADEMARK OFFICE

1711

Art Unit: 1711
Examiner: R. Sergeant

In Re Application of:

Applicant: LIU et al.

Serial No.: 09/546,174

Filed: April 11, 2000

For: HIGH DENSITY PLASMA
CHEMICAL VAPOR
DEPOSITION PROCESS

Docket No.: JIA 462C1

AMENDMENT

RECEIVED
JUL -3 2001

TC 1700 MAIL ROOM

July 2, 2001

Commissioner for Patents
Washington, DC 20231

Sir:

Responsive to the Office Action mailed April 3, 2001 please amend the application as follows.:

IN THE CLAIMS

Please cancel claims 1-20 without prejudice or disclaimer.

Please add new claims 21 - 37 as follows:

--21. (New) A method for forming isolated conductive structures on a substrate, comprising:

FEE ENCLOSED:
Please charge any further
fee to our Deposit Account
No. 18-0002